(POWER ELECTRONICS-DIE504)-End Term Examination-2024

Full Marks- 100: Time- 3 Hours

Answer Question No. 1 and any four from the remaining questions.

1.	a)	Fill up the blanks-	5 X 1 = 5
		i) The minority carriers in a p-n-p transistor are	
		ii) In a p-n junction, the depletion region will extend more towards the region having doping concentration.	
		iii) GTO is a/an switch.	
		iv) In a power transistor, current is the controlled parameter.	
		v) The value of anode current required in SCR to keep in the ON-state is called as	
	b)	Multiple choice questions-	5 X 1 = 5
		i) Which of the following does not belong to the thyristor family?	
		[A] SCR [B] SCS [C] IGBT [D] GTO	
		ii) In SCR, the forward breakover voltage is maximum when the Gate current is equal to-	
		[A] I _{gmin} [B] I _{gmax} [C] 0 [D] independent of Gate current	
		iii) Choose the false statement.	
		[A] SCR is a bidirectional device [B] SCR is a semi-controllable device	
		[C] SCR is used in high power applications	
		[D] SCR can be triggered with a light source	
		iv) Which of the following thyristors has an inbuilt avalanche diode between gate and cathode terminals?	
		[A] SCR [B] PUT [C] SUS [D] SCS	
		v) Which of the following switches can be used in a chopper circuit?	
		[A] BJT [B] MOSFET [C] GTO [D] All of these	
	c)	Answer the following questions in brief-	5 X 2 = 10
		i) What is the function of the drift region found in a power diode?	
		ii) State two differences between BJT and MOSFET.	
		iii) Define the term "holding current" for an SCR.	
		iv) State the intrinsic stand-off ratio of a Unijunction transistor.	
		v) What is the minimum anode voltage required to turn ON a PUT?	
2.	a)	What is the cause of reverse current in a diode even after the anode current becomes zero? Draw the reverse recovery characteristics diagram of a diode.	2 + 3 = 5
	b)	With the help of a diagram show how the gate current affects the the I-V characteristics of an SCR for at least four different values of gate current. (e.g. $Ig_4>Ig_3>Ig_2>Ig_1$)	5
	c)	Describe the various methods of turning ON an SCR.	5
	d)	What do you mean by time-constant of an R-C charging circuit? For an R-C charging circuit if-	5
		$Vs=10~V,~R=1~K\Omega$, and $C=2~mF$, calculate-	
		i) Time-constant ii) Capacitor voltage after 2 seconds (approximately)	

3.	a)	What is a thyristor firing circuit? Draw the Resistance firing circuit and find the values for R_1 and R for an SCR with the following parameters-	2 + 4 + 4 = 10
		Igm (Maximum gate current allowed) = 50 mA,	
		Vgm (Maximum gate voltage allowed) = 10 V,	
		Vm (Peak Anode Voltage) = 200 V,	
		Also, find out the peak gate voltage (Vgp) and the least firing angle (α) achievable with the firing circuit designed as above to turn-On the SCR (i.e. when $R_2=0$).	
	b)	Draw the physical structure and the equivalent circuit of a UJT and explain its working as a switch.	5
	c)	Derive the expression for the anode current of SCR with the help of the two-transistor model.	5
4.	a)	What is the main function of a DC chopper? Deduce the output voltage expression for an elementary chopper circuit.	6
	b)	With the help of voltage and current waveforms, explain the working of a single-phase half-wave rectifier circuit with 'R' load.	6
	c)	What is an inverter? Draw the circuit diagram of a single phase full-bridge inverter and explain its working.	8
5.	a)	Name the different thyristor commutation techniques. Briefly explain any one of these techniques.	2 + 5 = 7
	b)	For a half-wave rectifier circuit with R-L Load, draw the output current and voltage waveforms with respect to the input voltage and firing angle.	5
	c)	For a full-bridge inverter, draw the output current waveforms for the following types of loads-	4 X 2 = 8
		i) R ii) R-L iii) R-L-C over-damped and under-damped	
6.	a)	Draw the physical structure and explain how the conduction of current takes place in any four of the following power devices-	5 X 4 = 20
		i) GTO ii) Triac iii) IGBT	
		iv) PUT v) PMOSFET vi) SCR	

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